

9097250 TOSHIBA (DISCRETE/OPTO)

99D 16737 D

T-39-13



SEMICONDUCTOR

TECHNICAL DATA
TENTATIVE

TOSHIBA FIELD EFFECT TRANSISTOR

2 S K 6 7 4

SILICON N CHANNEL MOS TYPE
(π -MOS)

INDUSTRIAL APPLICATIONS

Unit in mm

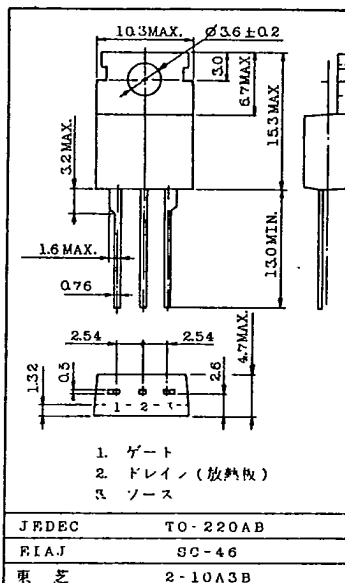
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.
CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR
DRIVE APPLICATIONS.

FEATURES:

- Low Drain-Source ON Resistance : $R_{DS(ON)}=0.040\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|=11S$ (Typ.)
- Low Leakage Current : $I_{GSS}=\pm 100nA$ (Max.) @ $V_{GS}=\pm 20V$
 $I_{DSS}=300\mu A$ (Max.) @ $V_{DS}=60V$
- Enhancement-Mode : $V_{th}=1.5\sim 3.5V$ @ $V_{DS}=10V, I_D=1mA$

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSX}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC($T_c=25^\circ C$)	I_D	A
	Pulse	I_{DP}	
Drain Power Dissipation ($T_c=25^\circ C$)	P_D	100	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ C$



THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	1.25	$^\circ C/W$
Thermal Resistance, Junction to Ambient	$R_{th(j-a)}$	83.3	$^\circ C/W$
Maximum Lead Temperature for Soldering Purposes (1.6mm from case for 10 seconds)	T_L	300	$^\circ C$

TOSHIBA CORPORATION

GT1A3A

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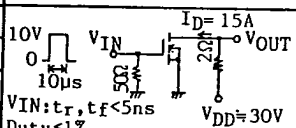
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SEMICONDUCTOR TECHNICAL DATA TENTATIVE

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ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain Cut-off Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	300	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	60	-	-	V
Gate Threshold Voltage	V_{th}	$V_{DS}=10V, I_D=1mA$	1.5	-	3.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=15A$	8.0	11	-	S
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D=15A, V_{GS}=10V$	-	0.040	0.060	Ω
Drain-Source ON Voltage	$V_{DS(ON)}$	$I_D=25A, V_{GS}=10V$	-	1.1	1.65	V
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	-	1200	1600	pF
Reverse Transfer Capacitance	C_{rss}		-	320	450	
Output Capacitance	C_{oss}		-	1200	1600	
Switching Time	Rise Time		-	80	160	ns
	Turn-on Time		-	100	200	
	Fall Time		-	85	170	
	Turn-off Time		-	165	330	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$I_D=25A, V_{GS}=10V$ $V_{DD}=48V$	-	38	60	nC
Gate-Source Charge	Q_{gs}		-	20	-	
Gate-Drain ("Miller") Charge	Q_{gd}		-	18	-	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	--	-	-	25	A
Pulse Drain Reverse Current	I_{DRP}	--	-	-	100	A
Diode Forward Voltage	V_{DSF}	$I_{DR}=25A, V_{GS}=0V$	-	-	1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR}=25A$	-	160	-	ns
Reverse Recovered Charge	Q_{rr}	$dI_{DR}/dt=100A/\mu s$	-	0.6	-	μC